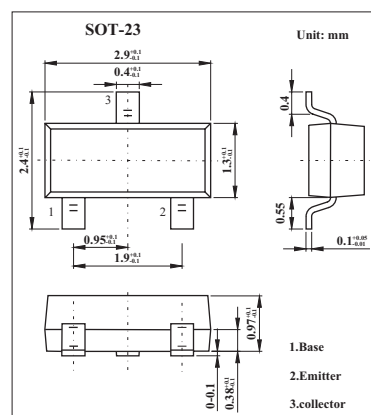


General Purpose Transistor

2SC2412

■ Features

- Low Cob.Cob=2.0pF (Typ.)



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	60	V
Collector-emitter voltage	V_{CEO}	50	V
Emitter-base voltage	V_{EBO}	7	V
Collector current	I_C	0.15	A
Collector power dissipation	P_C	0.2	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{CB0}	I _c =50μA	60			V
Collector-emitter breakdown voltage	V _{CE0}	I _c =1mA	50			V
Emitter-base breakdown voltage	V _{EB0}	I _E =50μA	7			V
Collector cutoff current	I _{CB0}	V _{CB} =60V			0.1	μA
Emitter cutoff current	I _{EB0}	V _{EB} =7V			0.1	μA
DC current Gain	h _{FE}	V _{CE} =6V, I _c =1mA	120		560	
Collector-emitter saturation voltage	V _{CE(sat)}	I _c /I _B =50mA/5mA			0.4	V
Collector Output Capacitance	C _{ob}	V _{CE} =12V, I _E =0A, f=1MHz		2	3.5	pF
Transition frequency	f _T	V _{CE} =12V, I _E =-2mA, f=100MHz		180		MHz

hFE Classification

Marking	BQ	BR	BS
Rank	Q	R	S
hFE	120 270	180 390	270 560